# Memory FRAM

# 256 K (32 K $\times$ 8) Bit

# MB85R256F

#### DESCRIPTIONS

The MB85R256F is an FRAM (Ferroelectric Random Access Memory) chip in a configuration of 32,768 words  $\times$  8 bits, using the ferroelectric process and silicon gate CMOS process technologies for forming the nonvolatile memory cells.

The MB85R256F is able to retain data without using a back-up battery, as is needed for SRAM.

The memory cells used in the MB85R256F can be used for 10<sup>12</sup> read/write operations, which is a significant improvement over the number of read and write operations supported by Flash memory and E<sup>2</sup>PROM.

The MB85R256F uses a pseudo - SRAM interface.

#### ■ FEATURES

- Bit configuration : 32,768 words × 8 bits
- Read/write endurance : 10<sup>12</sup> times / byte
- Data retention : 10 years (+85 °C), 95 years (+55 °C), over 200 years (+35 °C)
- Operating power supply voltage : 2.7 V to 3.6 V
- Low power consumption : Operating power supply current 5 mA (Typ)
  - Standby current 5 μA (Typ)
- Operation ambient temperature range: 40  $^{\circ}C$  to  $\,+$  85  $^{\circ}C$
- Package
- : 28-pin plastic SOP (FPT-28P-M17) 28-pin plastic SOP (FPT-28P-M01)
- : 28-pin plastic TSOP(1) (FPT-28P-M19)
  - Both are RoHS compliant



#### ■ PIN ASSIGNMENTS



#### **Functional description** Pin no. Pin name 1 to 10, 21, 23 to 26 A<sub>0</sub> to A<sub>14</sub> Address input pins I/Oo to I/O7 Data input/output pins 11 to 13, 15 to 19 CE 20 Chip enable input pin WE 27 Write Enable input pin 22 OE Output enable input pin 28 VDD Supply Voltage pin 14 GND Ground pin

#### ■ PIN FUNCTIONAL DESCRIPTIONS



#### BLOCK DIAGRAM



#### ■ FUNCTION LIST

Operation mode	CE	WE	ŌĒ	I/O <sub>0</sub> to I/O <sub>7</sub>	Power supply current
	Н	×	×		0, 1
Standby precharge	×	L	L	Hi-Z	Standby
	×	Н	Н		(102)
	L	۲	٦ ۲		
Latch address	٦¥	Н	L	—	—
	٦¥	L	Н		
Write	L	L	Н	Data input	Operation (les)
Read	L	Н	L	Data output	

H: High level, L: Low level,  $\times$ : can be either H, L,  $\checkmark$  or  $\checkmark$ , Hi-Z: High impedance,  $\checkmark$ : Latch address at falling edge

#### ■ ABSOLUTE MAXIMUM RANGES

Parameter	Symbol	Rat	Unit	
Faidilielei	Symbol	Min	Max	Unit
Power supply voltage*	Vdd	- 0.5	+ 4.0	V
Input voltage*	Vin	- 0.5	Vdd + 0.5	V
Output voltage*	Vout	- 0.5	Vdd + 0.5	V
Operation ambient temperature	TA	- 40	+ 85	°C
Storage temperature	Tstg	- 55	+ 125	°C

\*: These parameters are based on the condition that Vss is 0 V.

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

#### ■ RECOMMENDED OPERATING CONDITIONS

Baramotor	Symbol		Unit		
Faidilielei	Min		Тур	Max	Unit
Power supply voltage <sup>*1</sup>	Vdd	2.7	3.3	3.6	V
Operation ambient temperature*2	TA	- 40		+ 85	°C

\*1 : These parameters are based on the condition that  $V_{\text{SS}}$  is 0 V.

\*2 : Ambient temperature when only this device is working. Please consider it to be the almost same as the package surface temperature.

WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated within these ranges.

Always use semiconductor devices within their recommended operating condition ranges. Operation outside these ranges may adversely affect reliability and could result in device failure. No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their representatives beforehand.

### ■ ELECTRICAL CHARACTERISTICS

#### 1. DC Characteristics

#### (within recommended operating conditions)

<b>_</b>		hal Canditiana		Value			
Parameter Symbol Conditions		Conditions	Min	Тур	Max	Unit	
Input leakage current	u	$V_{IN} = 0 V \text{ to } V_{DD}$	—		10	μΑ	
Output leakage current	Ilo		—		10	μΑ	
Operating power supply current*1	lod	$\label{eq:cell} \begin{split} \overline{CE} &= 0.2 \text{ V},\\ \text{Other inputs} &= V_{\text{DD}} - 0.2 \text{ V}/0.2 \text{ V},\\ t_{\text{RC}} (\text{Min}), \text{ lout} &= 0 \text{ mA} \end{split}$		5	10	mA	
Standby current*2	lsв	$\overline{CE}, \overline{WE}, \overline{OE} \ge V_{DD}$	—	5	50	μΑ	
High level input voltage	Vih	V <sub>DD</sub> = 2.7 V to 3.6 V	$V_{\text{DD}}  imes 0.8$		$\begin{array}{c} V_{\text{DD}} + 0.5 \\ (\leq 4.0) \end{array}$	V	
Low level input voltage	VIL	V <sub>DD</sub> = 2.7 V to 3.6 V	- 0.5		+ 0.6	V	
High level output voltage	Vон	$I_{OH} = -2.0 \text{ mA}$	$V_{\text{DD}} \times 0.8$			V	
Low level output voltage	Vol	lo∟ = 2.0 mA	_		0.4	V	

\*1: During the measurement of IDD, the Address and Data In were taken to only change once per active cycle. Iout: output current

\*2: All pins other than setting pins shall be input at the CMOS level voltages such as  $H \ge V_{DD}$ ,  $L \le 0 V$ .

#### 2. AC Characteristics

AC Characteristics Test Condition

Power supply voltage: 2.7 V to 3.6 VOperation ambient temperature:- 40 °C to + 85 °CInput voltage amplitude: 0.3 V to 2.7 VInput rising time: 10 nsInput falling time: 10 nsInput evaluation level: VDD/2Output evaluation level: VDD/2Output Load Capacitance:10 pF

#### (1) Read cycle

Paramotor	Symbol	Va	lue	Unit
Falameter	Symbol	Min	Max	Unit
Read cycle time	<b>t</b> RC	150	—	
CE active time	<b>t</b> CA	70	500	
Read pulse width	<b>t</b> RP	70	500	
Precharge time	<b>t</b> PC	80	—	
Address setup time	tas	0		ne
Address hold time	tан	25	—	115
CE access time	<b>t</b> CE		70	
OE access time	toe	—	70	
CE output floating time	tнz	—	25	
OE output floating time	tонz		25	

#### (2) Write cycle

Baramotor	Symbol	Va	lue	Unit
Falameter	Symbol	Min	Max	Unit
Write cycle time	twc	150		
CE active time	<b>t</b> CA	70	500	
Write pulse width	twp	70	500	
Precharge time	t <sub>PC</sub>	80		ne
Address setup time	tas	0		115
Address hold time	tан	25		
Data setup time	tos	50		
Data hold time	tон	0	—	

## 3. Pin Capacitance

Baramotor	Symbol	Conditions		Unit		
Falameter	Symbol	Conditions	Min	Тур	Max	Unit
Input capacitance	CIN	$V_{DD} = V_{IN} = V_{OUT} = 0 V,$	—	—	10	pF
Output capacitance	Соит	$f = 1 \text{ MHz}, T_A = +25 ^{\circ}\text{C}$			10	pF



#### ■ TIMING DIAGRAM



#### 2. Read cycle (OE Control)



#### 3. Write cycle (CE Control)



#### 4. Write cycle (WE Control)



#### ■ POWER ON/OFF SEQUENCE



Paramotor	Symbol	Value			Unit	
Falameter	Symbol	Min	Тур	Max	Unit	
CE level hold time at power OFF	tpd	80	—	—	ns	
CE level hold time at power ON	tpu	80	—	—	ns	
Power supply rising time	tr	0.05	—	200	ms	

If the device does not operate within the specified conditions of read cycle, write cycle or power on/off sequence, memory data can not be guaranteed.

#### ■ FRAM CHARACTERISTICS

Item	Min	Max	Unit	Parameter
Read/Write Endurance*1	10 <sup>12</sup>		Times/byte	Operation Ambient Temperature $T_A = +85 \ ^{\circ}C$
	10	—		Operation Ambient Temperature $T_A = +85 \ ^{\circ}C$
Data Retention*2	95	—	Years	Operation Ambient Temperature $T_A = +55 \ ^{\circ}C$
	≥ 200			Operation Ambient Temperature $T_A = +35 \ ^{\circ}C$

\*1 : Total number of reading and writing defines the minimum value of endurance, as an FRAM memory operates with destructive readout mechanism.

\*2 : Minimum values define retention time of the first reading/writing data right after shipment, and these values are calculated by qualification results.

#### ■ NOTES ON USE

We recommend programming of the device after reflow. Data written before reflow cannot be guaranteed.

#### ■ ESD AND LATCH-UP

Test	DUT	Value
ESD HBM (Human Body Model) JESD22-A114 compliant		≥  2000 V
ESD MM (Machine Model) JESD22-A115 compliant		≥  200 V
ESD CDM (Charged Device Model) JESD22-C101 compliant		≥  1000 V
Latch-Up (I-test) JESD78 compliant	MB85R256FPF-G-BNDE1 MB85R256FPFCN-G-BNDE1	
Latch-Up (V <sub>supply</sub> overvoltage test) JESD78 compliant		
Latch-Up (Current Method) Proprietary method		≥  300 mA
Latch-Up (C-V Method) Proprietary method		_

• Current method of Latch-Up Resistance Test



Note : The voltage V<sub>IN</sub> is increased gradually and the current I<sub>IN</sub> of 300 mA at maximum shall flow. Confirm the latch up does not occur under I<sub>IN</sub> = ± 300 mA. In case the specific requirement is specified for I/O and I<sub>IN</sub> cannot be 300 mA, the voltage shall be increased to the level that meets the specific requirement. • C-V method of Latch-Up Resistance Test



Note : Charge voltage alternately switching 1 and 2 approximately 2 sec interval. This switching process is considered as one cycle.

Repeat this process 5 times. However, if the latch-up condition occurs before completing 5 times, this test must be stopped immediately.

#### ■ REFLOW CONDITIONS AND FLOOR LIFE

[ JEDEC MSL ] : Moisture Sensitivity Level 3 (ISP/JEDEC J-STD-020D)

#### ■ CURRENT STATUS ON CONTAINED RESTRICTED SUBSTANCES

This product complies with the regulations of REACH Regulations, EU RoHS Directive and China RoHS.

#### ■ ORDERING INFORMATION

Part number	Package	Shipping form	Minimum shipping quantity
MB85R256FPF-G-BNDE1	28-pin plastic SOP (FPT-28P-M17) Tube		*
MB85R256FPFCN-G-BNDE1	1 28-pin plastic TSOP(1) (FPT-28P-M19) Tray		*
MB85R256FPF-G-BND-ERE1	28-pin plastic SOP (FPT-28P-M17)	Embossed carrier tape	1000
MB85R256FPNF-G-JNE2	28-pin plastic SOP (FPT-28P-M01)	Tube	*
MB85R256FPNF-G-JNERE2	28-pin plastic SOP (FPT-28P-M01)	Embossed carrier tape	1000

\*: Please contact our sales office about minimum shipping quantity.



#### PACKAGE DIMENSIONS







28-pin plastic SOP	Lead pitch	1.27 mm
	Package width $\times$ package length	7.6  imes 17.75  mm
CREATER CONTRACTOR	Lead shape	Gullwing
	Sealing method	Plastic mold
	Mounting height	2.80 mm MAX
	Weight	0.67 g
(FPT-28P-M01)	Code (Reference)	P-SOP28-7.6×17.75-1.27



(Continued)

# MB85R256F

#### (Continued)





#### ■ MARKING











### PACKING INFORMATION

#### 1. Tube

#### 1.1 Tube Dimensions

Tube/stopper shape



#### Tube cross-sections and Maximum quantity

Package form	Packaga coda	Maximum quantity				
Fackage lotti	Fackage code	pcs/tube	pcs/inner box	pcs/outer box		
SOP, 28, plastic	FPT-28P-M17	28	2240	8960		
(10.6) $9.4$ $(6.8)$ $(6.8)$ $(6.8)$ $(6.8)$ $(10.6)$						
©2002-2010 FUJITSU SEMICONDUCTOR LIMITED F28011-SET1:FJ99L-0018-E0010-1-K-3						
t = 0.6						
Transparent polyvinyl chloride						

(Dimensions in mm)



#### 1.2 TUBE Dry pack packing specifications

\*1: For a product of witch part number is suffixed with "E1", a " G (B) " marks is display to the moisture barrier bag and the inner boxes.

\*2: The space in the outer box will be filled with empty inner boxes, or cushions, etc.

\*3: Please refer to an attached sheet about the indication label.

Note: The packing specifications may not be applied when the product is delivered via a distributor.

#### 1.3 Product label indicators

Label I: Label on Inner box/Moisture Barrier Bag/ (It sticks it on the reel for the emboss taping) [C-3 Label (50mm × 100mm) Supplemental Label (20mm × 100mm)]



Label II-A: Label on Outer box [D Label] (100mm × 100mm)



#### Label II-B: Outer boxes product indicate

XXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXX	Part number)		
(Lot Number) XXXX-XXX XXXX-XXX	(Count) X 箱 X 箱 計	(Quantity) XXX 個 XXX 個 XXX 個	

Note: Depending on shipment state, "Label II-A" and "Label II-B" on the external boxes might not be printed.

#### 1.4 Dimensions for Containers

#### (1) Dimensions for inner box



L	W	Н
540	125	75

(Dimensions in mm)

#### (2) Dimensions for outer box



L	W	Н
565	270	180

(Dimensions in mm)



# MB85R256F

#### 2. Tray

#### 2.1 Tray Dimensions





2.2 IEC (JEDEC) TRAY Dry Pack Packing Specifications

- \*1: For a product of witch part number is suffixed with "E1", a " G 🛞 " marks is display to the moisture barrier bag and the inner boxes.
- \*2: The size of the outer box may be changed depending on the quantity of inner boxes.
- \*3: The space in the outer box will be filled with empty inner boxes, or cushions, etc.
- \*4: Please refer to an attached sheet about the indication label.
- \*5: The packing materials except tray may differ slightly from the color and dimensions depend on country of manufacture.
- Note: The packing specifications may not be applied when the product is delivered via a distributor.

#### 2.3 Product label indicators

Label I: Label on Inner box/Moisture Barrier Bag/ (It sticks it on the reel for the emboss taping) [C-3 Label (50mm × 100mm) Supplemental Label (20mm × 100mm)]



Label II-A: Label on Outer box [D Label] (100mm × 100mm)



#### Label II-B: Outer boxes product indicate

XXXXXXXXXXXXXXX (P	art number)		
(Lot Number) XXXX-XXX XXXX-XXX	(Count) X箱 X箱	(Quantity) XXX 個 XXX 個 XXX 個	

Note: Depending on shipment state, "Label II-A" and "Label II-B" on the external boxes might not be printed.

#### 2.4 Dimensions for Containers

#### (1) Dimensions for inner box



L	W	Н
165	360	75
	-	(Dimensions in mm)

#### (2) Dimensions for outer box



L	W	Н
355	385	195
		<u>.</u>

(Dimensions in mm)

#### 3. Tape

#### 3.1 Tape Dimensions



#### 3.2 IC orientation



## 3.3 Reel dimensions



		-	_	_		_							D	imensior	ns in mm
Reel No	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15
Tape width Symbol	8	1	2	1	6	2	24	3	2	4	4	56	12	16	24
A	254 ± 2	254 ± 2	330 ± 2	254 ± 2	330 ± 2	254 ± 2	330 ± 2				330	±2			
В				1	00 <del>+</del> 2			100 -0	150 <sup>+2</sup>	100 +2	150 <sup>+2</sup> -0	100 +2		100 ± 2	
С		13 ± 0.2								<b>13</b> <sup>+0.5</sup> <sub>-0.2</sub>					
D		21 ± 0.8								20.5 +1 -0.2					
E		2 ± 0.5													
W1	$\begin{array}{ c c c c c c c c c c c c c c c c c c c$						12.4 +1	16.4 +1	24.4+0.1						
W2	less than 14.4	less that	an 18.4	less th	an 22.4	less the	an 30.4	less tha	an 38.4	less that	an 50.4	less than 62.4	less than 18.4	less than 22.4	less than 30.4
W3	7.9 ~ 10.9	11.9 ·	~ 15.4	15.9	~ 19.4	23.9	~ 27.4	31.9 ~	- 35.4	43.9 -	- 47.4	55.9 ~ 59.4	12.4 ~ 14.4	16.4 ~ 18.4	24.4 ~ 26.4
r		1.0													



#### 3.4 Taping (\u03e9330mm Reel) Dry Pack Packing Specifications

\*1: For a product of witch part number is suffixed with "E1", a " G ()" marks is display to the moisture barrier bag and the inner boxes.

\*2: The size of the outer box may be changed depending on the quantity of inner boxes.

\*3: The space in the outer box will be filled with empty inner boxes, or cushions, etc.

\*4: Please refer to an attached sheet about the indication label.

Note: The packing specifications may not be applied when the product is delivered via a distributor.



#### 3.5 Product label indicators

Label I: Label on Inner box/Moisture Barrier Bag/ (It sticks it on the reel for the emboss taping) [C-3 Label (50mm × 100mm) Supplemental Label (20mm × 100mm)]

XXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXX	← C-3 Label
(3N)2 XXXXXXXXX XXXXXX (FJ control number) XXX pcs (Quantity) XXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXX	<ul> <li>Perforated line</li> <li>Supplemental Label</li> </ul>

Label II-A: Label on Outer box [D Label] (100mm × 100mm)



#### Label II-B: Outer boxes product indicate

XXXXXXXXXXXXXXXXX	(Part number)		
(Lot Number) XXXX-XXX XXXX-XXX	(Count) X箱 X箱 計	(Quantity) XXX 個 XXX 個 XXX 個	

Note: Depending on shipment state, "Label II-A" and "Label II-B" on the external boxes might not be printed.

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#### 3.6 Dimensions for Containers

#### (1) Dimensions for inner box



Tape width	L	W	Н
12, 16			40
24, 32	365	345	50
44		545	65
56			75

(Dimensions in mm)

#### (2) Dimensions for outer box



L	W	Н
415	400	315

(Dimensions in mm)

#### ■ MAJOR CHANGES IN THIS EDITION

A change on a page is indicated by a vertical line drawn on the left side of that page.

Page	Section	Change Results
1	■ DESCRIPTIONS	Deleted the "compatible with conventional asynchronous SRAM".
5	■ RECOMMENDED OPERATING CONDITIONS	Added note on the Operation Ambient Temperature. Moved the "High Level Input Voltage" and "Low Level Input Voltage" to DC Characteristics.
6	1. DC Characteristics	Moved the "High Level Input Voltage" and "Low Level Input Voltage" from RECOMMENDED OPERATING CONDITIONS.
13	■ CURRENT STATUS ON CONTAINED RESTRICTED SUBSTANCES	Deleted the URL info.







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